

**APT6035BN 600V 19.0A 0.35Ω**

## POWER MOS IV®

### N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

#### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT6035BN	UNIT
$V_{DSS}$	Drain-Source Voltage	600	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	19	Amps
$I_{DM}$	Pulsed Drain Current ①	76	
$V_{GS}$	Gate-Source Voltage	$\pm 30$	Volts
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	310	Watts
	Linear Derating Factor	2.5	W/°C
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	°C
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )	600			Volts
$I_D(\text{ON})$	On State Drain Current ② ( $V_{DS} > I_D(\text{ON}) \times R_{DS}(\text{ON})$ Max, $V_{GS} = 10V$ )	19			Amps
$R_{DS}(\text{ON})$	Drain-Source On-State Resistance ② ( $V_{GS} = 10V, 0.5 I_D$ [Cont.])			0.35	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}, V_{GS} = 0V$ )			250	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )			$\pm 100$	nA
$V_{GS}(\text{TH})$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 1.0\text{mA}$ )	2		4	Volts

#### THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.40	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

**CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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**DYNAMIC CHARACTERISTICS**

**APT6035BN**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		2400	2950	pF
$C_{oss}$	Output Capacitance			436	610	
$C_{rss}$	Reverse Transfer Capacitance			154	230	
$Q_g$	Total Gate Charge <sup>③</sup>	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		87	130	nC
$Q_{gs}$	Gate-Source Charge			11	16	
$Q_{gd}$	Gate-Drain ("Miller") Charge			46	69	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 1.8\Omega$		14	28	ns
$t_r$	Rise Time			23	46	
$t_d(\text{off})$	Turn-off Delay Time			63	95	
$t_f$	Fall Time			23	46	

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$I_S$	Continuous Source Current (Body Diode)			19	Amps
$I_{SM}$	Pulsed Source Current <sup>①</sup> (Body Diode)			76	
$V_{SD}$	Diode Forward Voltage <sup>②</sup> ( $V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$ )			1.3	Volts
$t_{rr}$	Reverse Recovery Time ( $I_S = -I_D [\text{Cont.}]$ , $di_S/dt = 100A/\mu s$ )	152	334	668	ns
$Q_{rr}$	Reverse Recovery Charge ( $I_S = -I_D [\text{Cont.}]$ , $di_S/dt = 100A/\mu s$ )	2.5	5	10	$\mu C$

**SAFE OPERATING AREA CHARACTERISTICS**

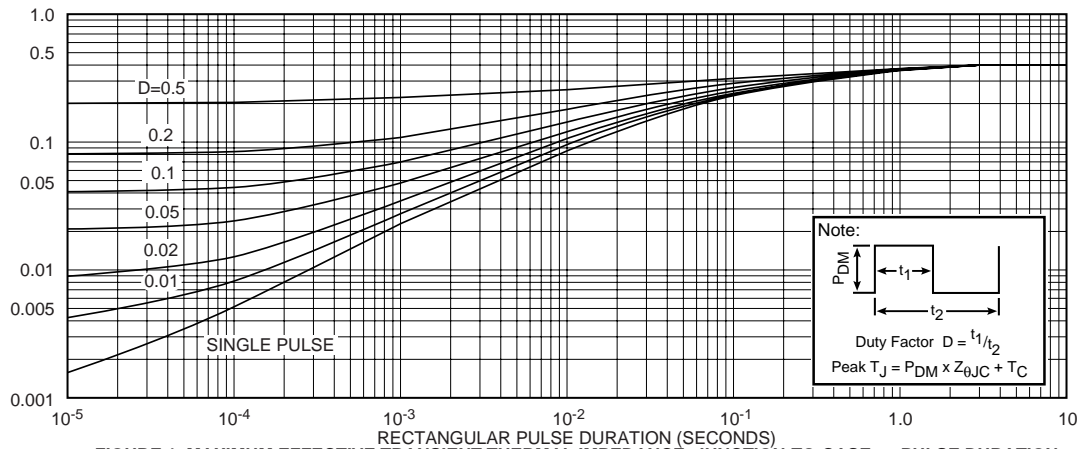
Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1\text{ Sec.}$	310			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D [\text{Cont.}], V_{DS} = P_D / I_D [\text{Cont.}], t = 1\text{ Sec.}$	310			
$I_{LM}$	Inductive Current Clamped		76			Amps

① Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)

② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%

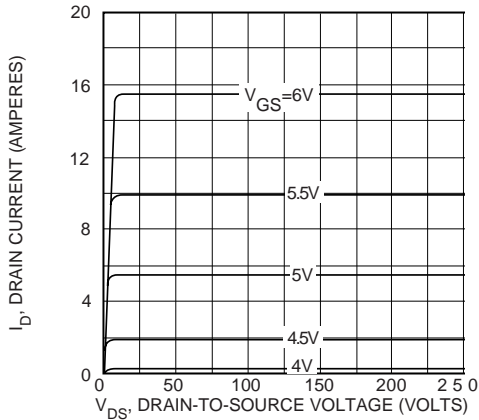
③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.

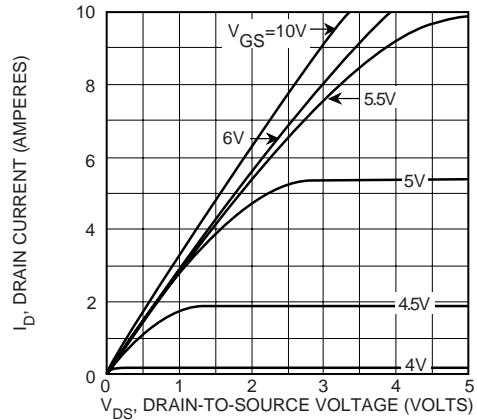


**FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION**

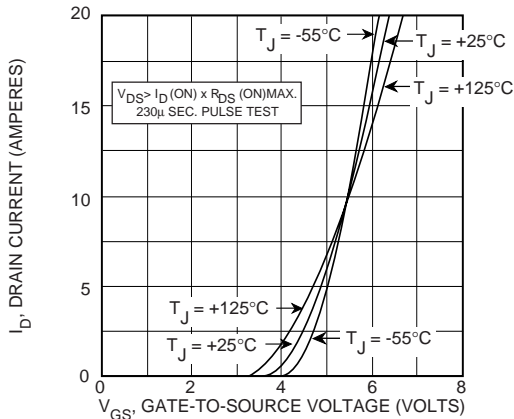
**APT6035BN**



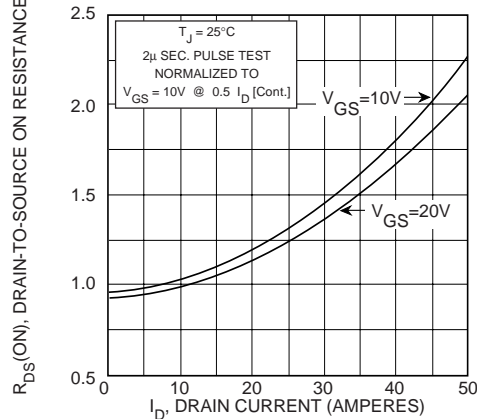
**FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS**



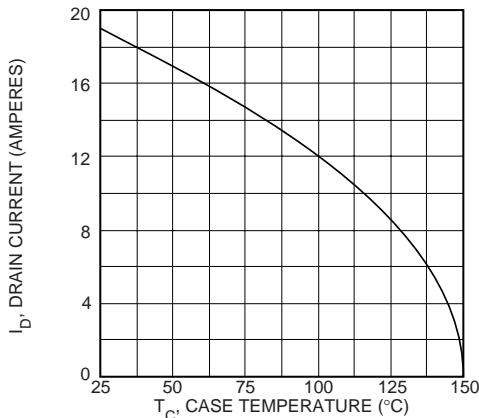
**FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS**



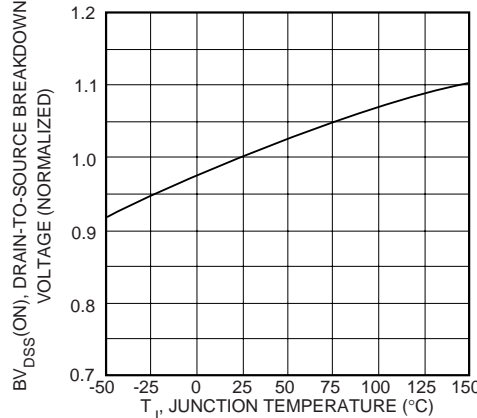
**FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS**



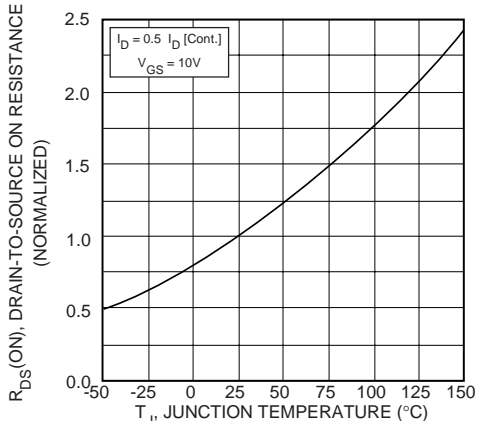
**FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT**



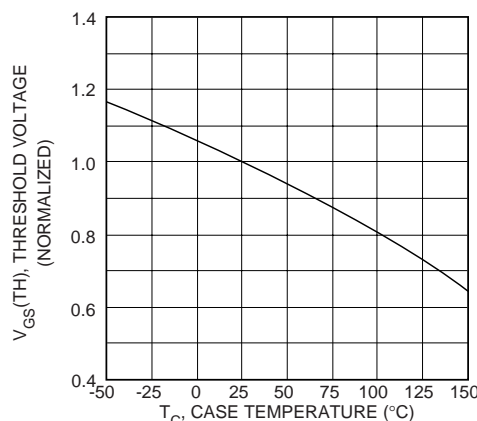
**FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE**



**FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE**

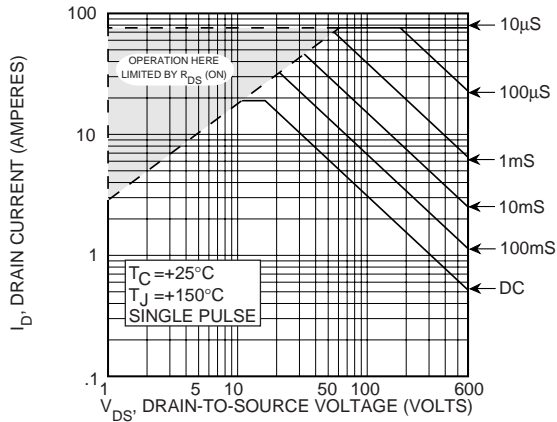


**FIGURE 8, ON-RESISTANCE vs. TEMPERATURE**

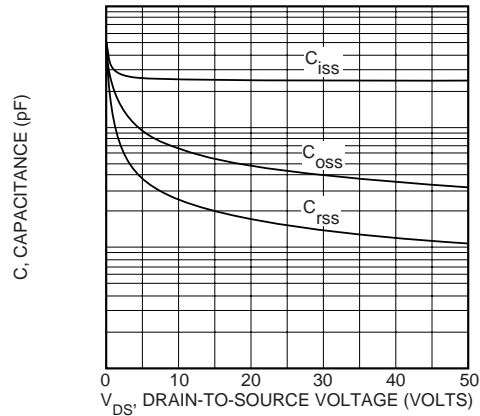


**FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE**

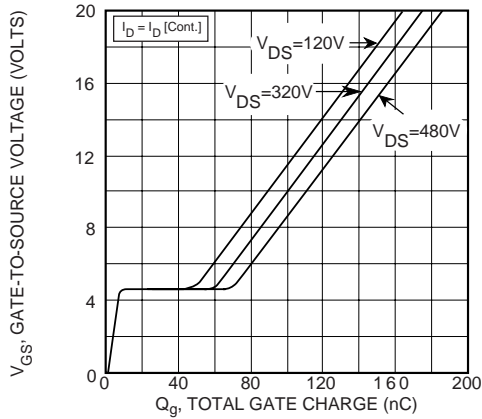
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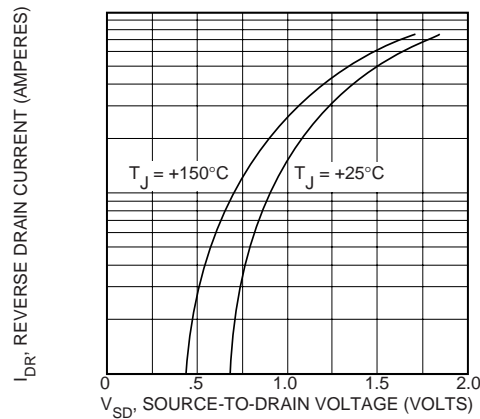
**FIGURE 10, MAXIMUM SAFE OPERATING AREA**



**FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE**

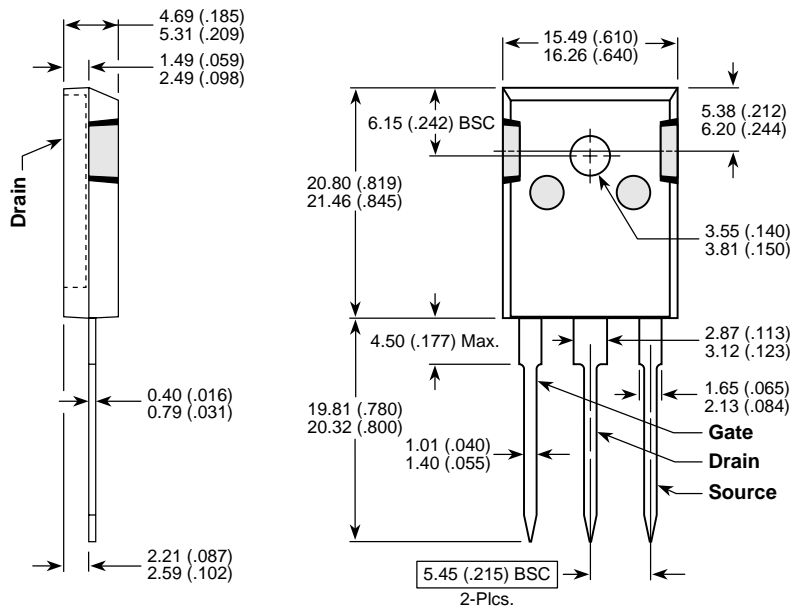


**FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE**



**FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE**

**TO-247AD Package Outline**



Dimensions in Millimeters and (Inches)



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